

بالے۲۱ میں کو - دانشگاهشهرکرد 24<sup>th</sup> Iranian Conference on Optics and Photonics (ICOP 2018) and 9<sup>th</sup> Iranian Conference on Photonics Engineering and Technology (ICPET 2018) Jan 30 - Feb 1, 2018 - Shahrekord University



# بررسی سه بعدی اثرات تغییر دما و ماده انتقال دهنده حفره بر عملکرد سلول خورشیدی پروسکایت

سوما زندی'، محمد رزاقی'

گروه مهندسی برق، دانشکده مهندسی، دانشگاه کردستان، سنندج

چکیده – اخیرا سلولهای خورشیدی مبنی بر ارگانو متال هالید پروسکایتها، پیشرفتهای چشمگیری داشتهاند. این ساختارها ویژگیهایی همچون چگالی نقص پایین، قابلیت تحرک بالای حاملها و طیف جذبی گسترده، را دارا هستند. در این مقاله، تکنیک عددی سه بعدی تفاضلهای محدود، برای شبیه سازی سلولهای خورشیدی پروسکایت مسطح، استفاده شده است. مدل تلفیقی الکتریکی و نوری برای تشخیص پارامترهای کلیدی سلول خورشیدی شبیهسازی شده استفاده می شود. تأثیر تغییرات دما، و جایگزینی مادهی است. با مادهی صادی کی و تری های خورشیدی بررسی شده است. تغییر مادهی ذکر شده منجر به تغییر ای و FF شده است. با توجه به نتایج شبیه سازیها، بهترین بازده ۸ ۱۴/۳۲ برای سلول خورشیدی حاصل می شود.

کلید واژه- سلول خورشیدی، پروسکایت، دما، شبیه سازی سه بعدی و HTM.

## 3D Investigation of Temperature and Hole Transport Material Variation on Performance of Perovskite Solar Cell

Soma Zandi<sup>1</sup>, Mohammad Razaghi<sup>1</sup>

<sup>1</sup>Dept. of Electrical Eng., School of Engineering, University of Kurdistan, Sanandaj, Iran Email address: <u>soma.zandi@gmail.com</u> and mrazaghi@gmail.com

Abstract- Recently, organo-metal halide perovskite solar cells based on planar architecture have demonstrated an exceptional progress These structures show lower defect density, high carrier mobility, and broader absorption spectra in compare to other solar cells. In this work a 3D finite element method (FEM) technique is used to simulate a planer perovskite solar cell. Coupled electrical-optical modeling is constructed to fully characterize the proposed device. We investigate variation of short circuit current ( $J_{sc}$ ), open circuit voltage ( $V_{oc}$ ) and fill factor (*FF*) in different temperature ranges (280-340 K). Also, the effect of material replacement (Cu<sub>2</sub>O material instead of CuSCN), as hole transport material (HTM), has been investigated on solar cell performance. It is caused to change Jsc. Based on the result the best PCE is 14.32%. These simulation results open up a way to find accurate design parameters in solar cell with best performance.

Keywords: Solar cell, perovskite, temperature, 3D simulation and HTM



## 1 Introduction

Nowadays, Solid-state organo-metal halide perovskite solar cells (PSCs) have revolutionized solar cell industry. This new kind of solar cell such as MAPbX3 (MA= CH3NH3+; X = Cl<sup>-</sup>, Br<sup>-</sup>, I) has demonstrated an exceptional progress in solar cell power conversion efficiency (PCEs) from 3.81% for MAPbI<sub>3</sub> to over 20% [1, 2, 4]. high carrier mobility [3, 4], Long carrier diffusion length [3, 4], and long absorption coefficient [3, 4] are promising characteristics of perovskite materials..

Device simulation gives a better description of physical mechanism in solar cells. However, the number of reported simulations in this field are few. Therefore, in this work we present a threedimensional (3D) PSC based on the finite-element method (FEM) from the "COMSOL Multiphysics" software package. Firstly, we validate our simulation results with previous experimental investigations [5]. Then, the effect of temperature variation and hole transport material (HTM) changes, are examined. It is shown that these variations, have an effective role on design of high PCE PSCs.

## 2 Theory and modelling

A schematic of the solar cell structure has been represented in Fig. 1. As it can be seen in this figure, a n-i-p solar cell with TiO<sub>2</sub> n-type layer as electron transport material (ETM) laver. CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> as intrinsic layer and CuSCN p-type layer as HTM layer, is considered. Firstly, presented model is validated with previously published work [5]. Proposed n-i-p PSC structural parameters are taken as follow: a width of 250nm and a depth of 250 nm. Also, the structure includes five layers of: Air (500 nm thick), FTO (50 nm), TiO<sub>2</sub>(90 nm), CH<sub>3</sub> NH<sub>3</sub> PbI<sub>3</sub>(200 nm), CuSCN (600 nm,) and Au (100 nm), (see Fig. 1). Generally, our presented model consists of two parts of optical and electrical.

## 2.1 Optical Model

The Wave Optic module has been used in order to solve Maxwell's equations in the frequency domain. It is expressed as follow:

$$\nabla \times (\nabla \times E) - K_0^2 \varepsilon_r E = 0 \tag{1}$$

where, *E* is electric field,  $k_0$  is wave-vector and  $\varepsilon_r$  is Complex Relative Permittivity  $\varepsilon_r = (n-ik)^2$ , which is a function of wavelength ( $\lambda$ ).



Figure 1: A schematic of perovskite solar cell (PSC).

With known amount of *E*, the photo-generation rate per each wavelength  $(G_{photo} (\lambda))$ , can be calculated as follow:

$$G_{photo}(\lambda) = \frac{\varepsilon^{"} |E|}{2h}$$
(2)

where *h* is the plank constant,  $\varepsilon$ " is the imaginary part of the  $\varepsilon_r$ . For  $G_{photo}$  ( $\lambda$ ) calculation, AM1.5G was used as the input power. The complex refractive indexes of FTO, CuSCN, TiO<sub>2</sub>, CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> and Au are taken from previously measured data [6-9]. Total generation rate ( $G_{tot}$ ) is calculated by integration over the wavelength ranges. The results of these calculations have been presented in Fig. 2.

## 2.2 Electrical model

To evaluate current density-voltage (J-V) characteristics, semiconductor module from COMSOL software, is used. This module is based on solving Poisson and Continuity equations. It is expressed as below:

$$\nabla .(\varepsilon_s \nabla \phi) = -\rho \tag{3}$$

$$\frac{\partial n}{\partial t} = \frac{1}{q} \nabla j_n + G_n - U_n \tag{4}$$

$$\frac{\partial p}{\partial t} = \frac{1}{q} \nabla j_p + G_p - U_n \tag{5}$$

This paper is authentic if it can be found in www.opsi.ir.



where  $\phi$  is electrostatic potential. q is electron charge.  $\varepsilon_s$  is semiconductor permittivity,  $G_n$  and  $G_p$ are total generation rates,  $U_n$  and  $U_p$  are recombination rates of electron and holes respectively.  $\rho$  is a charge density,  $J_n$  and  $J_p$  are current density of electron and hole. Calculated amount of  $G_{tot}$  in wave optic module, is replaced with  $G_n$  and  $G_p$  in this part. The numerical parameters used in this part, are provided in Table1. All the parameters in Table 1 have been selected according to valid theoretical and experimental researches [3, 7, 10].

Parameter	TiO <sub>2</sub>	CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub>	CuSCN	Cu <sub>2</sub> O
$\varepsilon_s$	9	6.5	10	3
$N_c ({\rm cm}^{-3})$	$1 \times 10^{19}$	$1.66 \times 10^{19}$	$1.79 \times 10^{19}$	$1 \times 10^{19}$
$N_D (\mathrm{cm}^{-3})$	$1 \times 10^{19}$	$5.41 \times 10^{19}$	$2.51 \times 10^{19}$	$1 \times 10^{19}$
$\mu_n/\mu_p$ (cm <sup>2</sup> /V.S)	2/1	50/50	1×10 <sup>-4</sup> / 0.01	3.4/3.4
χ (eV)	4	3.93	1.9	3.4
$E_g$ (eV)	3.2	1.55	3.4	2.22
$\tau_n / \tau_p$ (ns)	5/5	8/8	5/5	5/5
$N_A ({\rm cm}^{-3})$	-	5×10 <sup>13</sup>	$5 \times 10^{18}$	5×10 <sup>18</sup>
$N_D ({\rm cm}^{-3})$	5×10 <sup>19</sup>	-	-	-

 Table1. The electrical parameters of PSC [3, 8, 11]

#### 3 Result and discussion

The current density-voltage (*J*-*V*) characteristic of the perovskite solar cell in 300 K, has been shown in Fig. 3. As it is depicted, the maximum PCE ( $PCE=FF*J_{sc}V_{oc}$ ), short-circuit current density ( $J_{sc}$ ), open-circuit voltage ( $V_{oc}$ ) and fill factor ( $FF=MPP/(J_{sc}V_{oc})$ ), have been reached to 14.32%, 18.77 (mA/cm<sup>2</sup>), 0.98 (V) and 0.78 respectively. The PCE of the simulated PSC shows a good matching with experimental result [5]. In addition, in this work CuSCN is replaced by a Cu<sub>2</sub>O as HTM layer [11]. The Complex refractive index of  $Cu_2O$  is taken from [12]. Electrical parameters of  $Cu_2O$  have been listed in Table1.

In Fig. 4, the current density-voltage characteristics of the simulated perovskite solar cell, (with two kinds of inorganic HTMs ( $Cu_2O$ , CuSCN)), have been shown.



Figure 3: J–V curve of perovskite solar cell.



Figure 4: J-V curve of PSC with different HTM layer.

As it is shown in the results, the  $J_{sc}$  is decreased when the Cu<sub>2</sub>O is used instead of CuSCN. This is due to total generation of carriers in perovskite layer. By using the Cu<sub>2</sub>O layer, due to the decrease of interface reflectivity of this layer and perovskite layer for portion of input frequency range (based on material characteristic's), less amount of incident optical field is reflected to perovskite layer. As a result, the carrier generation is decreased in perovskite layer.

Another study is examination of temperature effect on solar cell performance. Fig. 6 depicts the effect of temperature (T) on J-V characteristics of the PSC. As it can be seen when the T increases from 280 K to 340 K, the  $V_{oc}$  decreases while the  $J_{sc}$  remains roughly intact. This is mainly because of the  $V_{oc}$  dependency to the *T*. This relation can be found as below [13]:

$$V_{oc} = \frac{kT}{q} \ln\left(\frac{Jsc}{J_0(T)}\right) \tag{6}$$

where k is Boltzmann constant and  $J_0$  is a dark current density, which related to T, as below:

$$J_0 \approx B'' T^3 \exp\left(-\frac{E_{g0}}{kT}\right) \tag{7}$$

where B is a constant, that independent of T. So, temperature effect on the  $V_{oc}$  in solar cell is calculated as follow:

$$\frac{dV_{oc}}{dT} = -\frac{\left(V_{g0} - V_{OC}\right) + 3V_T}{T}$$
(8)



Figure 5: J-V curve of PSC as a function of temperature.

#### 3 Conclusion

In this work, 3D FEM simulation of PSC was performed. It causes to achieve more accurate results in light propagation and electrical performance of PSCs. It was shown that, by replacing Cu<sub>2</sub>O with CuSCN as HTM layer, the PCE is changed. In addition, as the temperature increased, due to  $V_{oc}$  reduction, the PCE of PSC is decreased.

#### References

- [1] Kojima, Akihiro, et al. "Organometal halide perovskites as visible-light sensitizers for photovoltaic cells," *Journal of the American Chemical Society*, vol. 131, no. 17, pp. 6050-6051, 2009.
- [2] F. Zhang et al., "Over 20% PCE perovskite solar cells with superior stability achieved by

novel and low-cost hole-transporting materials," *Nano Energy*, vol. 41, pp. 469-475, 2017

- [3] A. Zhang, Y. Chen, and J. Yan, "Optimal Design and Simulation of High-Performance Organic-Metal Halide Perovskite Solar Cells," *IEEE Journal of Quantum Electronics*, vol. 52, no. 6, pp. 1-6, 2016
- [4] Zuo, Chuantian, et al. "Advances in perovskite solar cells," *Advanced Science*, vol. 3, no. 7, 2016.
- [5] P. Qin *et al.*, "Inorganic hole conductor-based lead halide perovskite solar cells with 12.4% conversion efficiency," *Nature communications*, vol. 5, p. ncomms4834, 2014.
- [6] S. Wenger, Sophie, et al. "Coupled optical and electronic modeling of dye-sensitized solar cells for steady-state parameter extraction," *The Journal of Physical Chemistry C*, vol. 115, no. 20, pp. 10218-10229, 2011
- [7] P. Pattanasattayavong *et al.*, "Electric fieldinduced hole transport in copper (I) thiocyanate (CuSCN) thin-films processed from solution at room temperature," *Chemical Communications*, vol. 49, no. 39, pp. 4154-4156, 2013.
- [8] J. M. Ball *et al.*, "Optical properties and limiting photocurrent of thin-film perovskite solar cells," *Energy & Environmental Science*, vol. 8, no. 2, pp. 602-609, 2015.
- [9] Rakić, Aleksandar D., et al. "Optical properties of metallic films for vertical-cavity optoelectronic devices," *Applied optics*, vol. 37, no. 22, pp. 5271-5283, 1998.
- [10] Q. Zhou *et al.* "Two-dimensional device modeling of CH 3 NH 3 PbI 3 based planar heterojunction perovskite solar cells," *Solar Energy*, vol. 123, pp. 51-56, 201.
- [11] P. Vivo, J. K. Salunke, and A. Priimagi, "Hole-Transporting Materials for Printable Perovskite Solar Cells," *Materials*, vol. 10, no. 9, p. 1087, 2017.
- [12] Xiang, Chengxiang, et al. "820 mV opencircuit voltages from Cu 2 O/CH 3 CN junctions," *Energy & Environmental Science*, vol. 4, no. 4, pp. 1311-1318, 2011.
- [13] G. Siefer and A. W. Bett, "Analysis of temperature coefficients for III–V multi- junction concentrator cells," *Progress in Photovoltaics: Research and Applications*, vol. 22, no. 5, pp. 515-524, 2014

This paper is authentic if it can be found in www.opsi.ir.